



The diagram illustrates a 1T1R1W1D memory cell circuit. It features a central crossbar structure. A horizontal line at the top is labeled "write word line". A horizontal line below it is labeled "read word line". A vertical line on the left is labeled "write digit line". A vertical line on the right is labeled "read digit line". The circuit includes several transistors and inverters. Transistors 101 and 102 are connected to the write word line and the write digit line. Transistors 107 and 108 are connected to the read word line and the read digit line. Inverters 103 and 104 are connected to the write digit line and the read digit line. The circuit is designed to store a single bit of data, with the write word line and write digit line used for writing and the read word line and read digit line used for reading.

FIG. 2
PRIOR ART

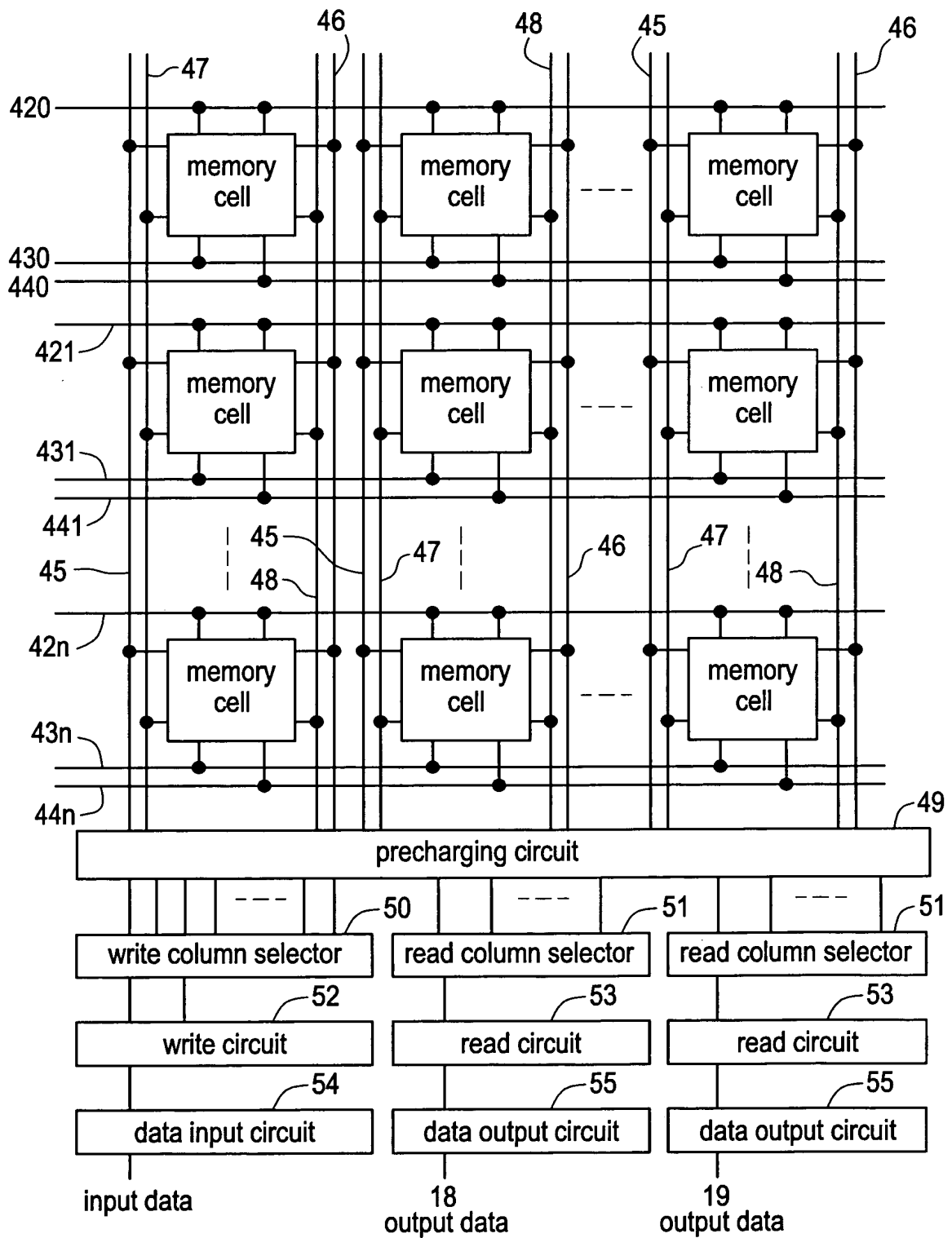


FIG. 3
PRIOR ART

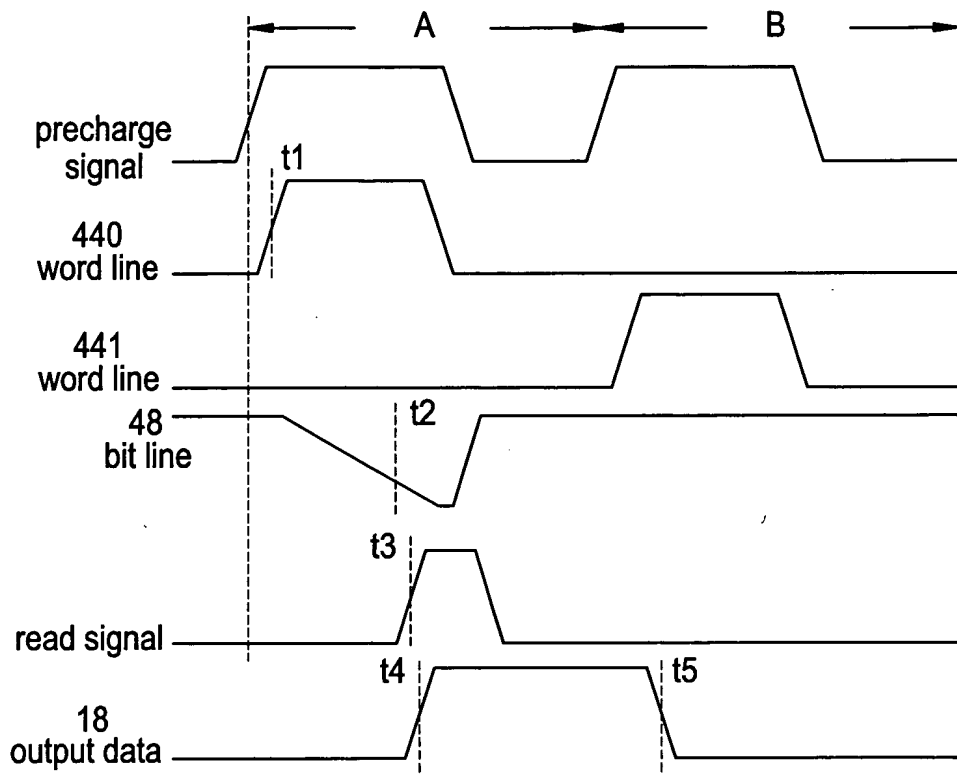
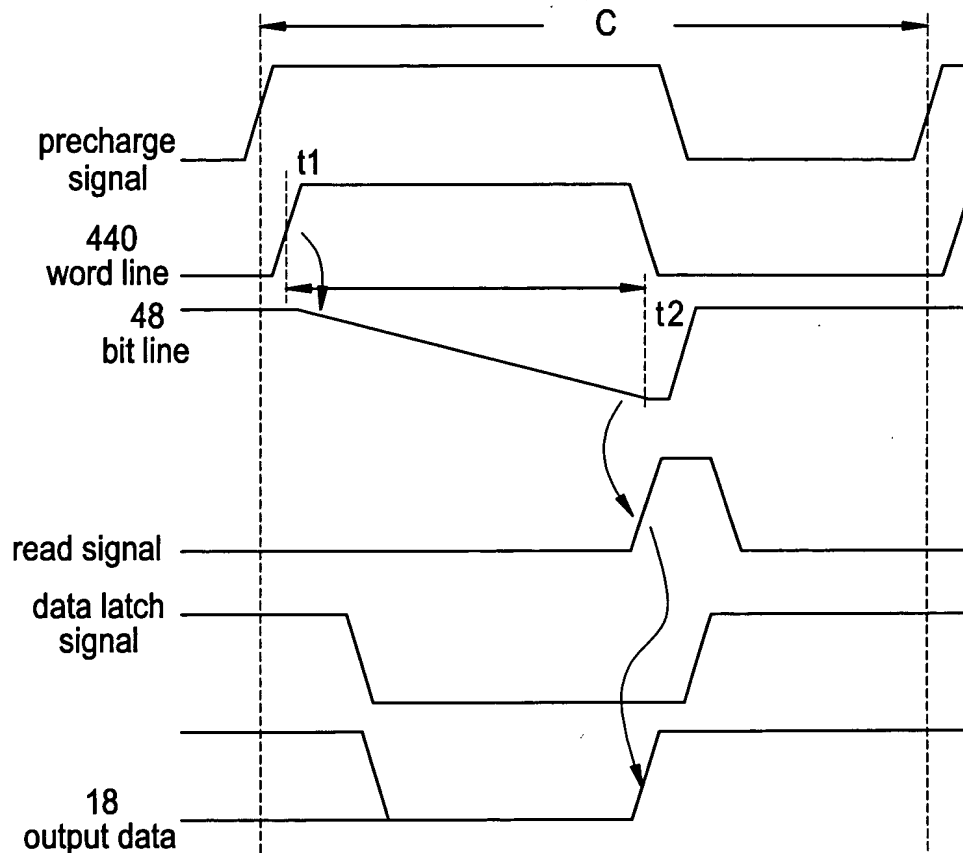


FIG. 4



5/15

FIG. 5
PRIOR ART

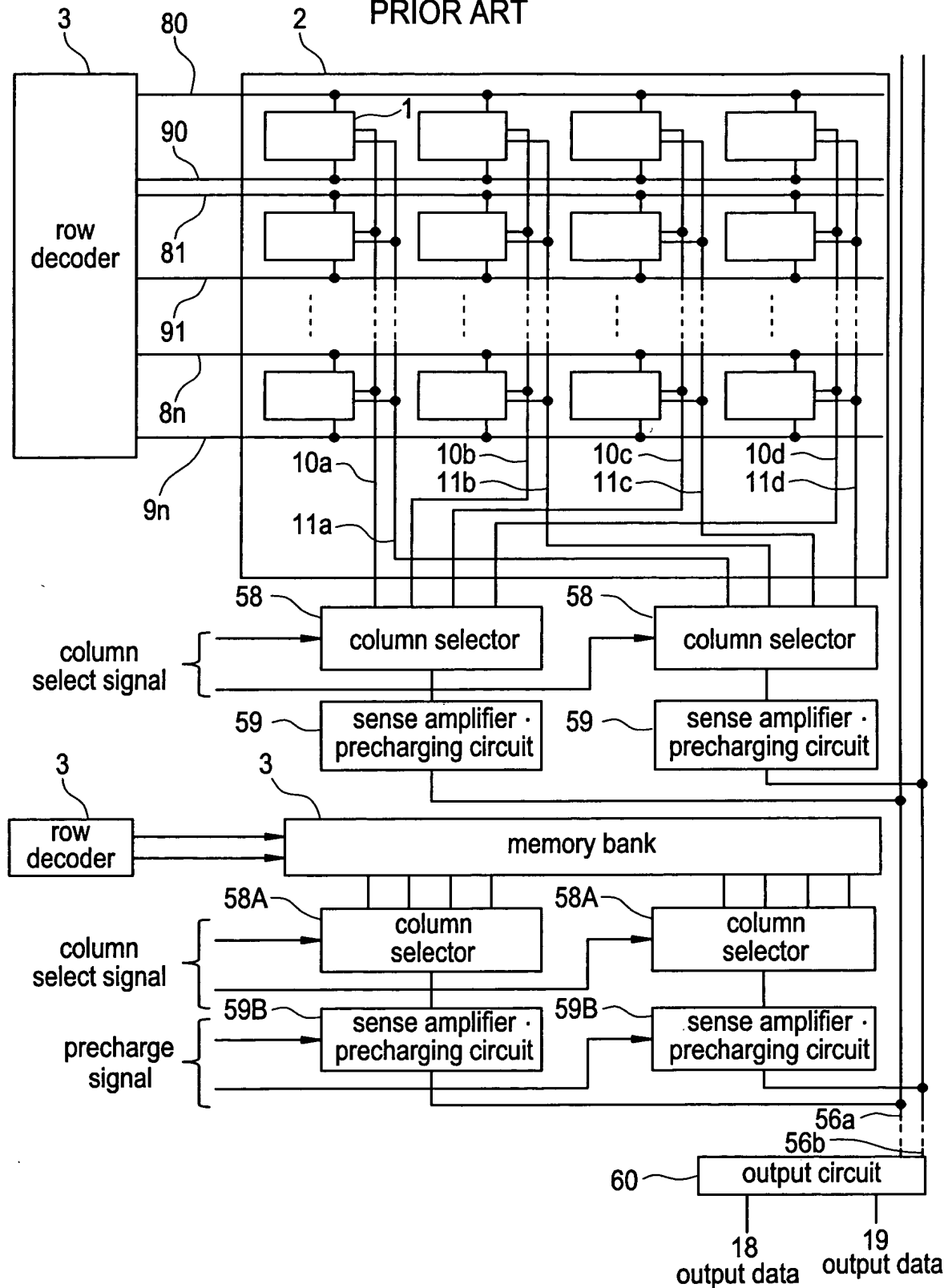


FIG. 6
PRIOR ART

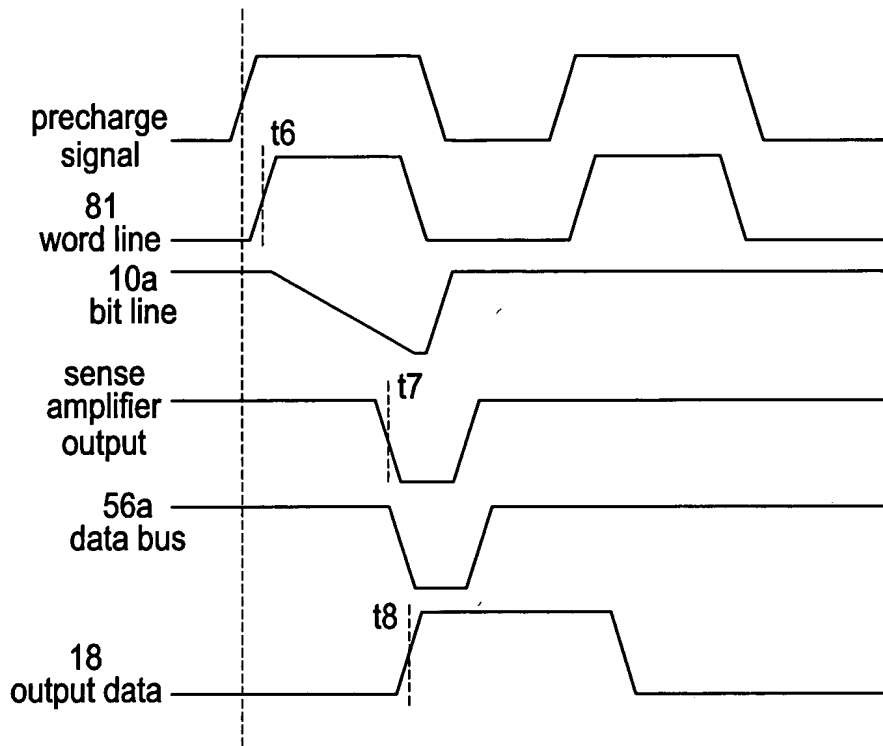


FIG. 7
PRIOR ART

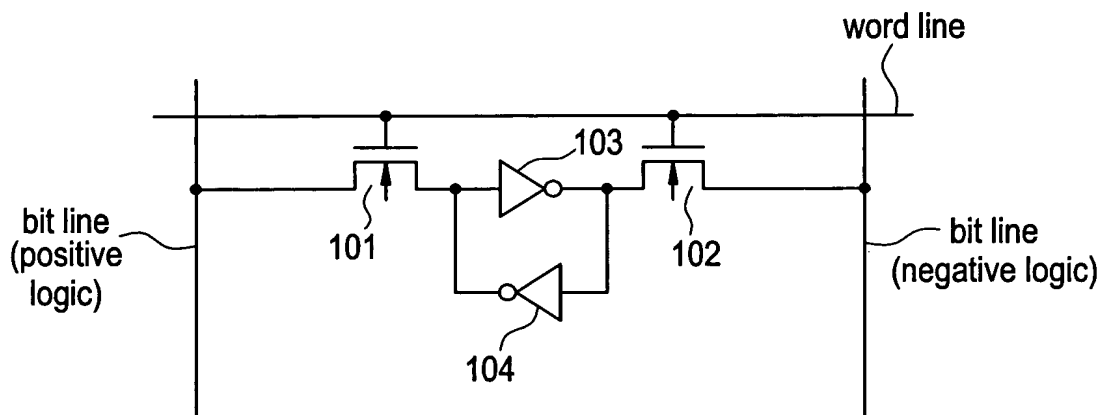


FIG. 8

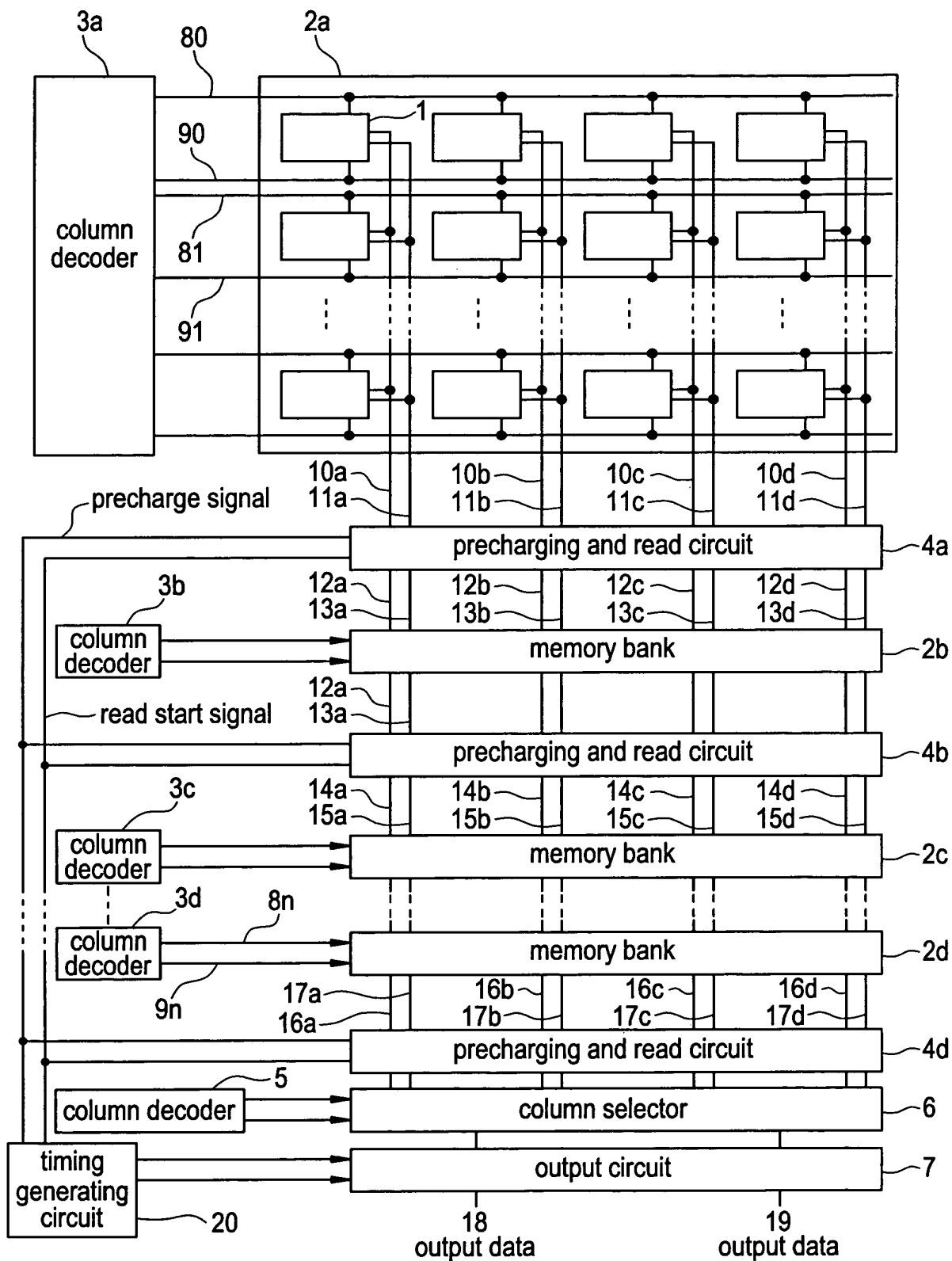


FIG. 9

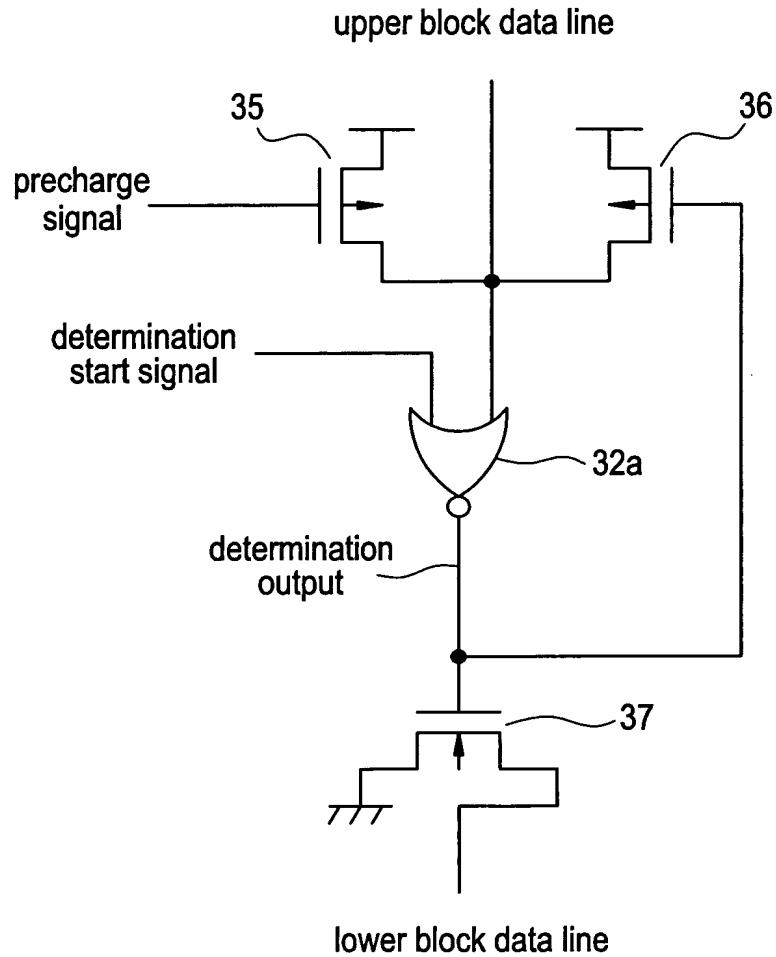


FIG. 10

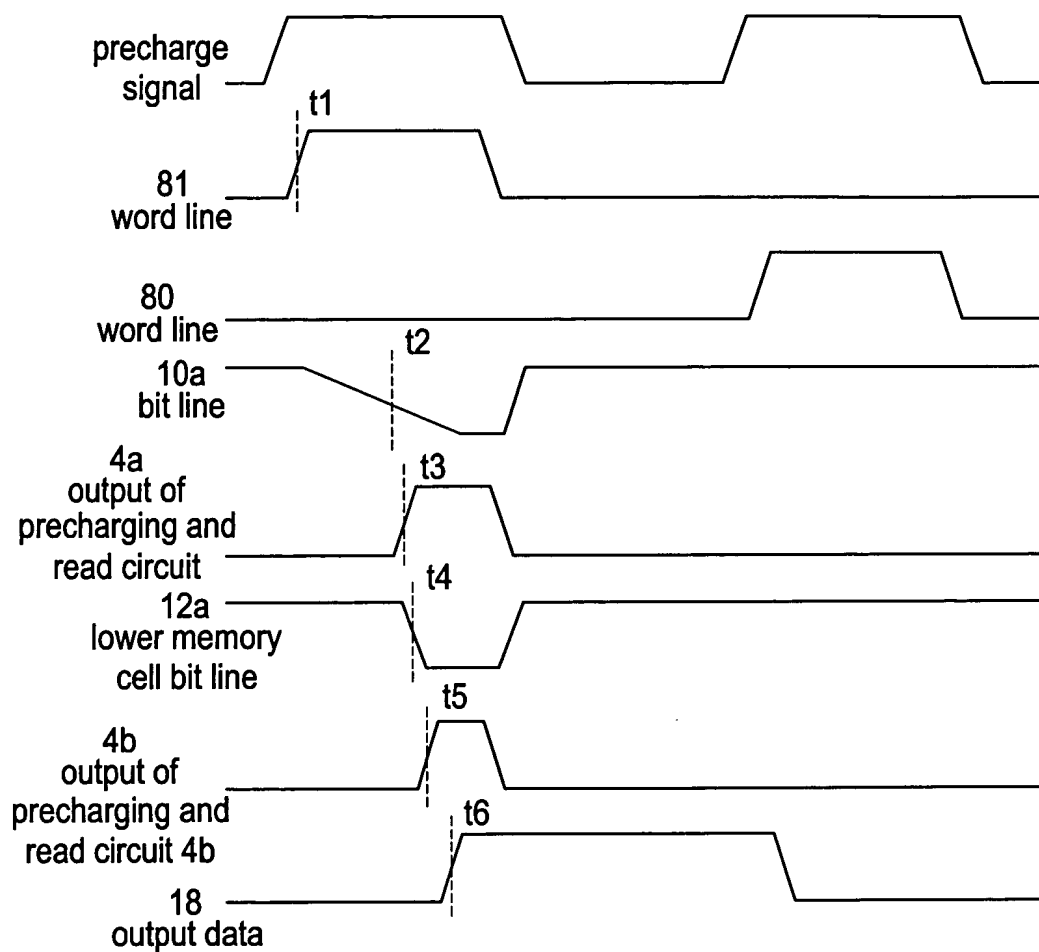


FIG. 11

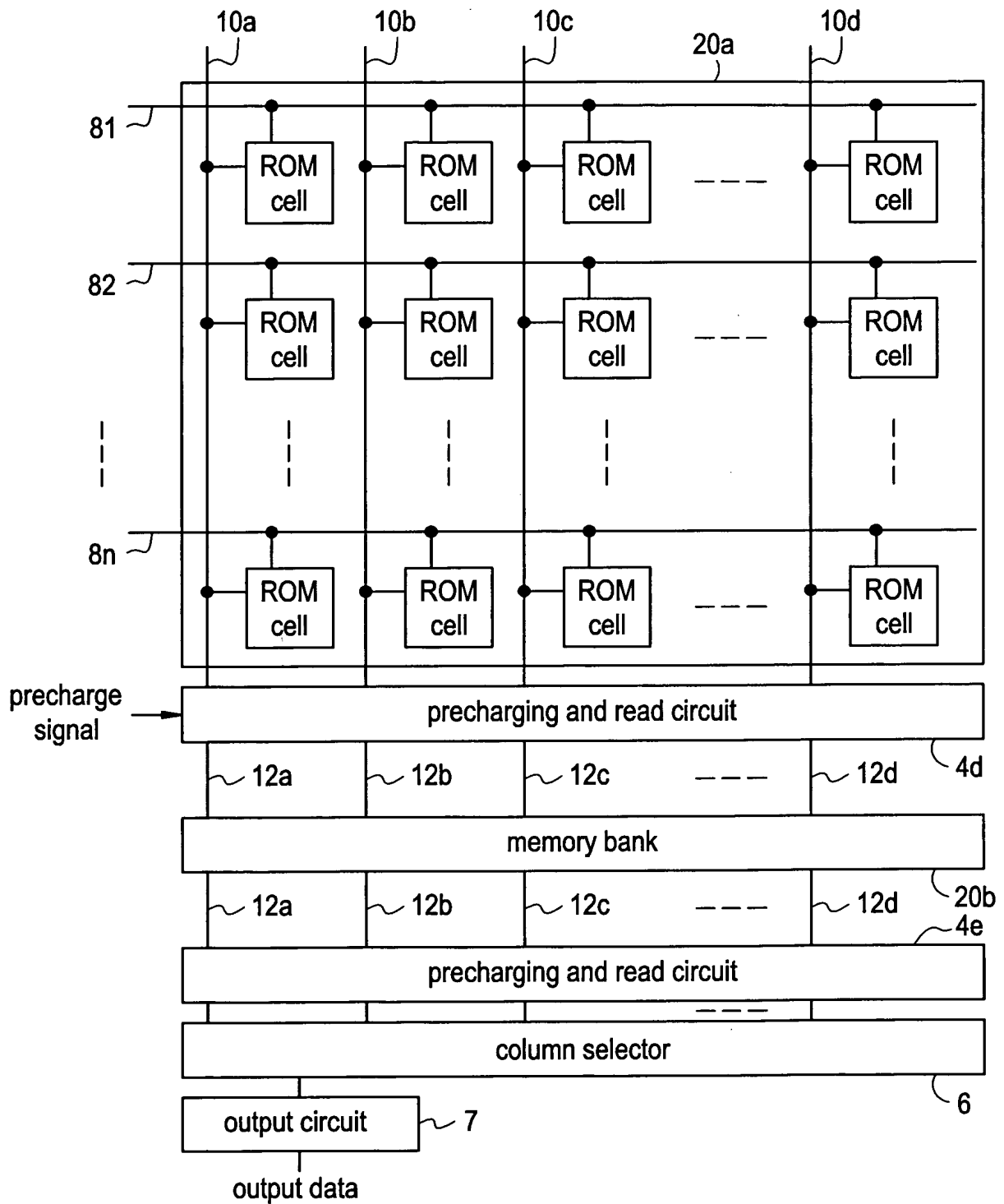
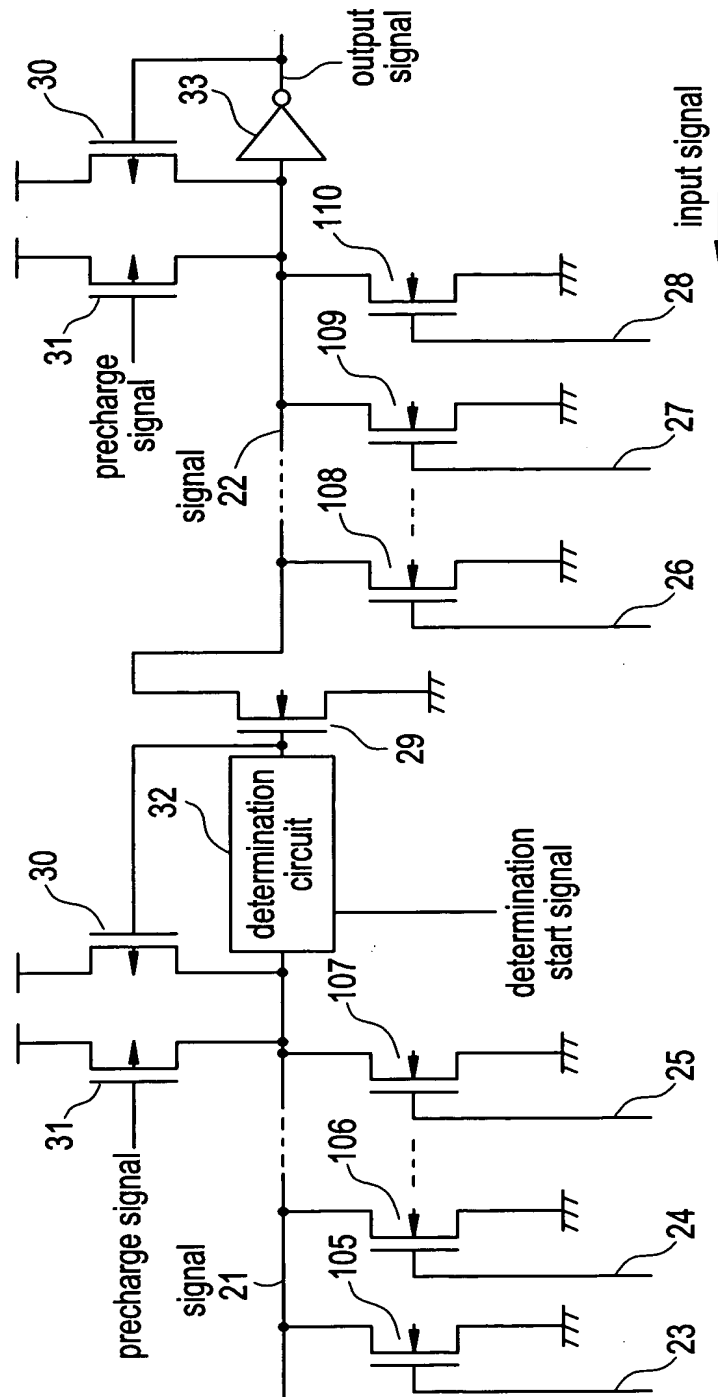


FIG. 12



12/15

FIG. 13

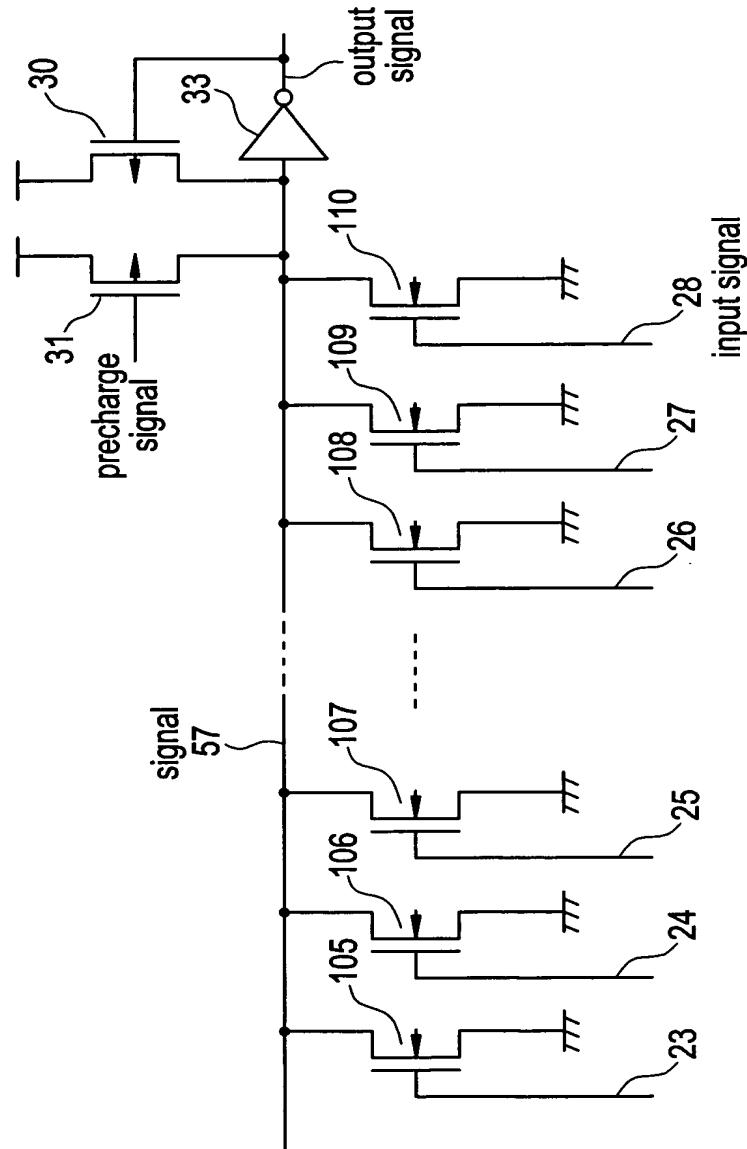


FIG. 14

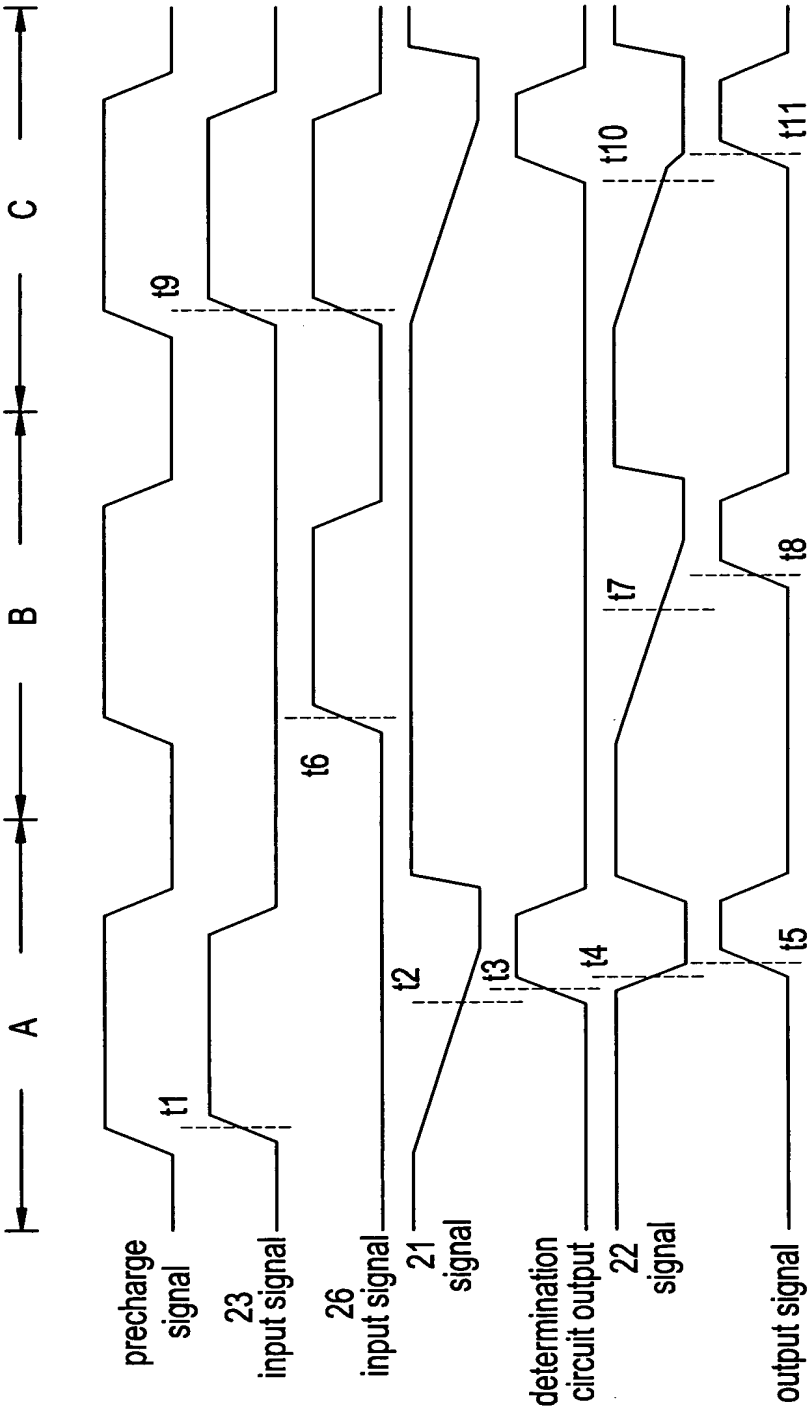
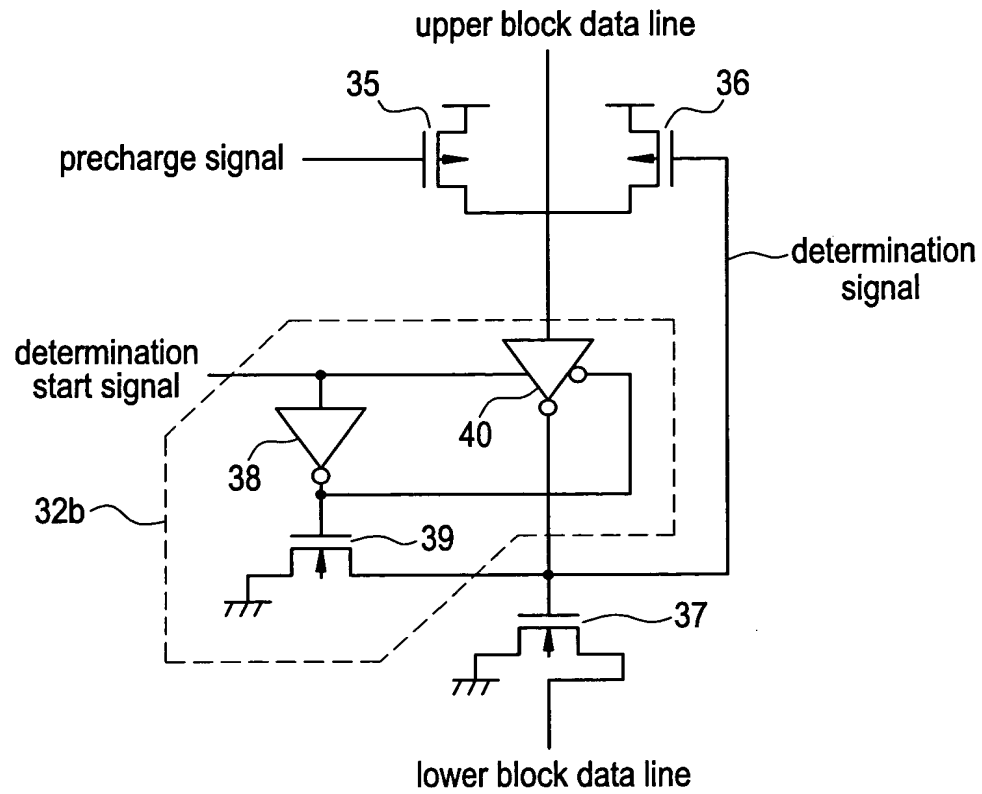


FIG. 15



upper block data line

precharge signal

reference signal

determination start signal

35

36

32c

38

39

40

41

determination signal

lower block data line